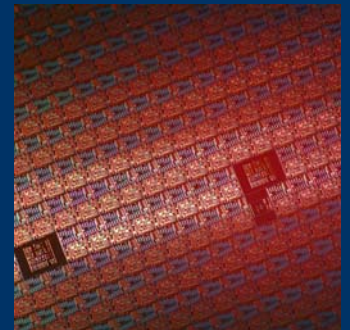




# Resist Outgassing Working Group Introduction

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# Scope of Working Group



## Purpose

- A forum to discuss issues related to testing methods of resist outgassing, understand the risks of resist outgassing, and drive consensus within the community.

## Goals

- Standardize testing methods to achieve a common accepted testing methodology using best known/determined practices
- Drive consensus among tool manufacturers to a common metric and test method for resist outgassing
- Confirm or dismiss the risks of outgassing resist as a contributor to optics contamination
  - Identify the materials from the resist that cause contamination



# Contributors



## Tool Manufacturers

- **ASML**                      **Noreen Harned**
- **Canon**                      **Akira Miyake**
- **Nikon**                      **Takashi Aoki**

## Resources

- **CNSE**                      **Greg Denbeaux**
- **IMEC**                      **Ivan Pollentier**
- **NIST**                      **Charles Tarrío**  
**Thomas Lucatorto**  
**Shannon Hill**
- **SELETE**                      **Iwao Nishiyama**
- **SEMATECH**                      **Emil Piscani**  
**Jacque Georger**



# Resist Outgassing Concerns



## for MET Tools

- **Outgassing not a concern for these low power, low WPH tools**
- **Replacement of illuminator optics has been enough to restore power to the wafer, no degradation of the PO has been noted**

## for HVM Tools

- **For overall optics contamination, there are potential sources from both hardware and resist**
  - **hardware outgassing may diminish over time (but repairs)**
  - **resist is a continuous source of outgassing (100WPH)**
- **Increased intensity throughout system increases risk of species conversion to carbonaceous layers**



# Resist Outgassing Specifications



## ASML

- **2E14 molecules/(cm<sup>2</sup>sec) for hydrocarbons >45AMU for ADT access**
- **Incident wafer plane power of 10mW/cm<sup>2</sup> for the ADT**

## Canon/Nikon

- **3E13 molecules/(cm<sup>2</sup>sec) for hydrocarbons >45AMU**
- **Incident wafer plane power of 600mW/cm<sup>2</sup> for HVM**
- **Resist is ~10% contribution of total outgassing budget**

## SEMATECH

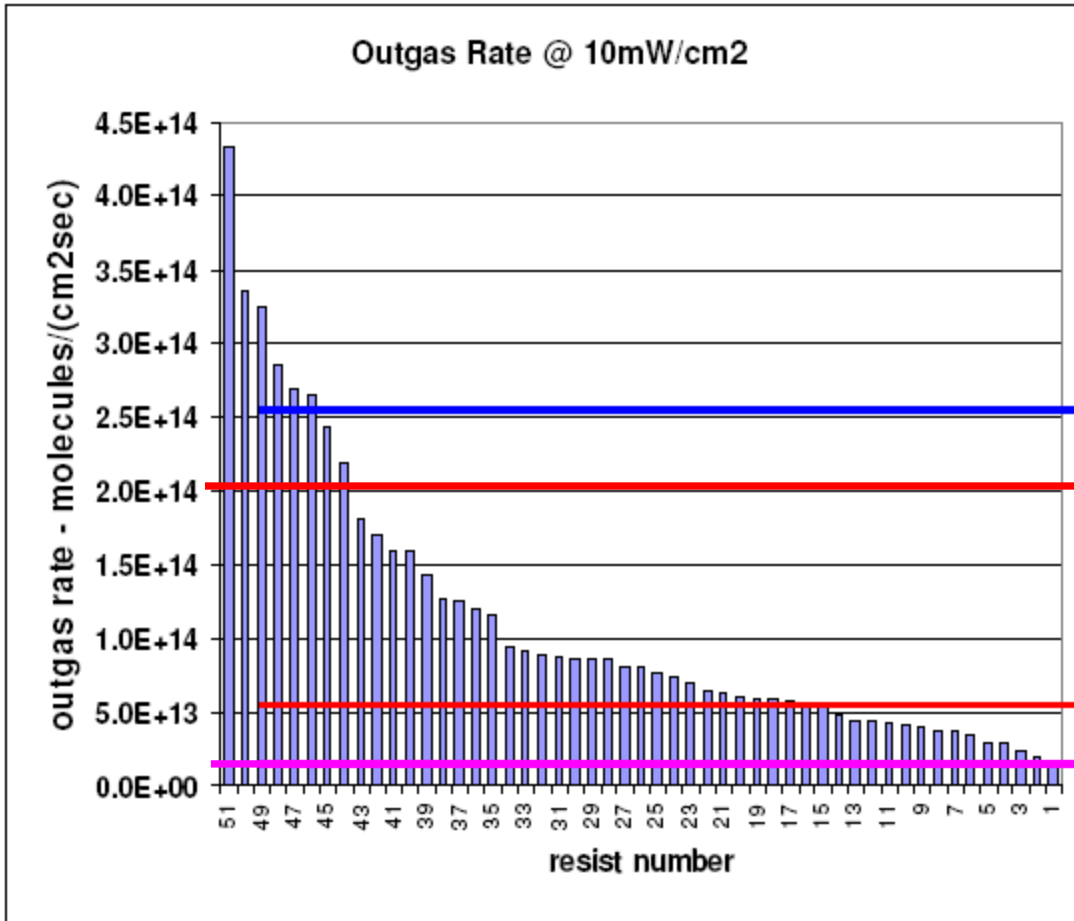
- **6.5E14 molecules/(cm<sup>2</sup>sec)**



# Resist Outgassing Specifications



2E15  
(10mW/cm<sup>2</sup>)



SEMATECH spec  
converted to rate based  
upon 10 mW/cm<sup>2</sup> power  
level of Alpha/Beta tools

SEMATECH  
2007 spec

2E14  
(10mW/cm<sup>2</sup>)

ASML  
original spec

3E13  
(600mW/cm<sup>2</sup>)

Nikon  
original spec

Orvek, TWG, 2008

# Resist TWG Guidance



- Continue cycles of learning in resist and materials development to address challenges of RLS to achieve Z parameter ( $nZ_{32}$ ) targets
- At this time, outgassing should not be a primary concern for resist development
  - MET tools will support material development
  - best performing materials may be overlooked



# Thank you



## Thank you for your attention!

